



## Subject card

Subject name and code	Semiconductor Devices, PG_00047563						
Field of study	Biomedical Engineering						
Date of commencement of studies	October 2024	Academic year of realisation of subject			2025/2026		
Education level	first-cycle studies	Subject group			Obligatory subject group in the field of study		
Mode of study	Full-time studies	Mode of delivery			at the university		
Year of study	2	Language of instruction			Polish		
Semester of study	3	ECTS credits			1.0		
Learning profile	general academic profile	Assessment form			assessment		
Conducting unit	Department of Microelectronic Systems -> Faculty of Electronics, Telecommunications and Informatics						
Name and surname of lecturer (lecturers)	Subject supervisor		dr inż. Łukasz Gołuński				
	Teachers		dr inż. Łukasz Gołuński				
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	Project	Seminar	SUM
	Number of study hours	0.0	0.0	15.0	0.0	0.0	15
	E-learning hours included: 0.0						
Learning activity and number of study hours	Learning activity	Participation in didactic classes included in study plan		Participation in consultation hours		Self-study	SUM
	Number of study hours	15		1.0		9.0	25
Subject objectives	Learning through experiments of the operation principles of basic semiconductor devices and learning the methods of measuring their characteristics, as well as learning methods of determining values of their equivalent circuits, useful in designing of electronic circuits.						

Learning outcomes	Course outcome	Subject outcome	Method of verification
	[K6_U02] can perform tasks related to the field of study in an innovative way as well as solve complex and nontypical problems, applying knowledge of physics, in changing and not fully predictable conditions	Student measures and analyzes static characteristics of diodes and transistors. Student measures and analyzes processes of switching in circuits with diodes or with transistors. Student measures and analyzes small signal amplifying properties of transistors in dependence on frequency. Student measures characteristics and analyzes properties of electroluminescent diodes. Student measures characteristics and analyzes operation of photodiodes, photoelements and optical relays in application circuits.	[SU2] Assessment of ability to analyse information [SU1] Assessment of task fulfilment
	[K6_U03] can design, according to required specifications, and make a simple device, facility, system or carry out a process, specific to the field of study, using suitable methods, techniques, tools and materials, following engineering standards and norms, applying technologies specific to the field of study and experience gained in the professional engineering environment	Student measures and analyzes static characteristics of diodes and transistors. Student measures and analyzes processes of switching in circuits with diodes or with transistors. Student measures and analyzes small signal amplifying properties of transistors in dependence on frequency. Student measures characteristics and analyzes properties of electroluminescent diodes. Student measures characteristics and analyzes operation of photodiodes, photoelements and optical relays in application circuits.	[SU4] Assessment of ability to use methods and tools [SU1] Assessment of task fulfilment
	[K6_U06] can analyse the operation of components, circuits and systems related to the field of study, measure their parameters and examine technical specifications	Student measures and analyzes static characteristics of diodes and transistors. Student measures and analyzes processes of switching in circuits with diodes or with transistors. Student measures and analyzes small signal amplifying properties of transistors in dependence on frequency. Student measures characteristics and analyzes properties of electroluminescent diodes. Student measures characteristics and analyzes operation of photodiodes, photoelements and optical relays in application circuits.	[SU4] Assessment of ability to use methods and tools [SU1] Assessment of task fulfilment
Subject contents	Static characteristics of semiconductor diodes. Switching characteristics of semiconductor diodes. Properties of stabilization diodes. IV characteristics of field effect transistors and extraction of parameters for their equivalent circuits. Small signal operation of transistors for small and medium frequencies. Pulse operation and models of transistors. Characteristics and models of electroluminescent diodes and photodiodes.		
Prerequisites and co-requisites			
Assessment methods and criteria	Subject passing criteria	Passing threshold	Percentage of the final grade
	Reports of experiments	50.0%	100.0%
Recommended reading	Basic literature	Our laboratory instruction booklets. Ch. Papadopoulos, "Solid-State Electronic Devices: An Introduction", Springer 2014 J.-P. Colinge, C.A. Colinge, "Physics of Semiconductor Devices", Springer 2002	
	Supplementary literature	M. Grundmann, The Physics of Semiconductors: An Introduction Including Nanophysics and Applications, 2ed., Springer 2010 A.S. Sedra, K.C. Smith, "Microelectronic Circuits", Oxford, 2007 Ch.C. Hu, Modern Semiconductor Devices for Integrated Circuits, Prentice Hall 2009	
	eResources addresses	Adresy na platformie eNauczanie:	
Example issues/ example questions/ tasks being completed	Connect a circuit presented on a diagram in the instruction booklet. The output voltage value of the generator should be adjusted so that the peak-peak value of $V_{ce}$ is 100 mV at $f = 1$ kHz. Take a record of the generator voltage $V_{gpp}$ . Use it to calculate the low-frequency value of $h_{21e0}$ . Measure and plot the dependence of $ h_{21e} $ on frequency. Determine experimentally the $\beta_{beta}$ value. Calculate values of the emitter-base diffusion capacitance $C_{difE}$ , the common-emitter current-gain cut-off frequency $f_T$ , and the electron transit time $t_{tn}$ .		
Work placement	Not applicable		